

RESPONSE TO RESTRICTION REQUIREMENT and
AMENDMENT UNDER 37 C.F.R. § 1.111
U.S. Application No. 09/986,332

REMARKS

Claims 1-4, 6, 8-12, 16, 17, 23, 25, 48, 49, 177-185, 187, and 188-207 are all the claims pending in the application. This Amendment amends claims 49, and adds claims 189-207. No claims are canceled.

In response to the restriction requirement, dated May 2, 2002, Applicant elects Group I, including claims 1-4, 6, 8-12, 16-17, 23, 25, 48-49, and 189-207 for examination. Claims 189-207 are added in this Amendment, and all depend from Group I claims. This election is made without traverse.

Applicant reserves the right to file a Divisional Application directed to non-elected claims 177-185, 187-188.

If any points remain in issue which the Examiner feels may be best resolved through a personal or telephone interview, the Examiner is kindly requested to contact the undersigned at the telephone number listed below.

The USPTO is directed and authorized to charge all required fees, except for the Issue Fee and the Publication Fee, to Deposit Account No. 19-4880. Please also credit any overpayments to said Deposit Account.

Respectfully submitted,



David A. Klein
Registration No. 46,835

SUGHRUE MION, PLLC
2100 Pennsylvania Avenue, N.W.
Washington, D.C. 20037-3213
Telephone: (202) 293-7060
Facsimile: (202) 293-7860

Date: September 25, 2002

RESPONSE TO RESTRICTION REQUIREMENT and
AMENDMENT UNDER 37 C.F.R. § 1.111
U.S. Application No. 09/986,332

APPENDIX

Version With Markings To Show Changes Made

IN THE CLAIMS:

The claims are amended as follows:

49. (Amended) A method according to claim 48, wherein:

a total area of upper surfaces of portions, of the underlayer, which are covered with said first selective growth mask is larger than that of portions, of the underlayer, which are exposed from the first windows[,];

[and] a total area of upper surfaces of portions, of the first nitride semiconductor portions, which are covered with said second selective growth mask is larger than that of portions, of the first nitride semiconductor portions, which are exposed from the second windows;

a total area covered by said second selective growth mask is larger than an area of said first selective growth mask; and

said first selective growth mask and said second selective growth mask are positioned such that a combination of said first selective growth mask and said second selective growth mask is over or covers a total surface area of said underlayer.

Claims 189-207 are added as new claims.